

isc Silicon NPN Power Transistors

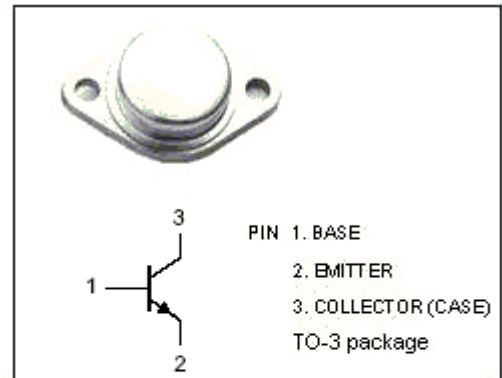
2SD673

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 100V(\text{Min})$
- High Power Dissipation-
: $P_C = 60W(\text{Max})@T_C=25^\circ\text{C}$
- Complement to Type 2SB653

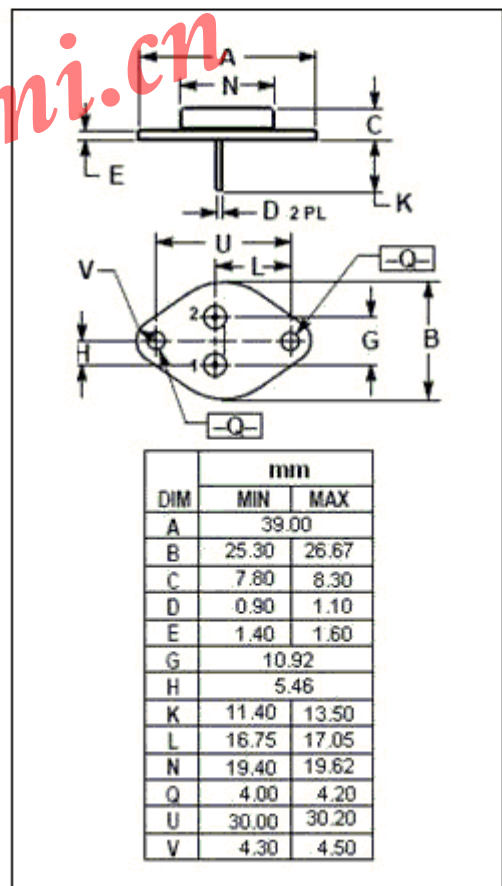
APPLICATIONS

- Designed for low frequency power amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 120 | V |
| V_{CEO} | Collector-Emitter Voltage | 100 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 7 | A |
| I_{CM} | Collector Current-Peak | 12 | A |
| I_B | Base Current-Continuous | 2 | A |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 60 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ\text{C}$ |



isc Silicon NPN Power Transistors**2SD673****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 50mA; R _{BE} = ∞ | 100 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 5mA; I _C = 0 | 5 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 0.5A | | | 3.0 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 1A; V _{CE} = 5V | | | 1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 100V; I _E = 0 | | | 1 | mA |
| h _{FE-1} | DC Current Gain | I _C = 1A; V _{CE} = 5V | 60 | | 200 | |
| h _{FE-2} | DC Current Gain | I _C = 5A; V _{CE} = 5V | 20 | | | |

◆ **h_{FE-1} Classifications**

| B | C |
|--------|---------|
| 60-120 | 100-200 |